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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/022,722	
			Filing Date	December 20, 2001	
			First Named Inventor	Glen Hush	
			Art Unit	2818	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	M4065.0481/P481

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HK	A	6,469,364 B1	10/22/2002	Kozicki	
HK	B	US 2002/0168820 A1	11/14/2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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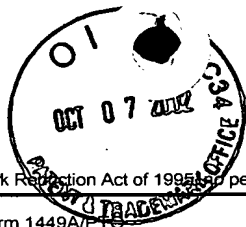
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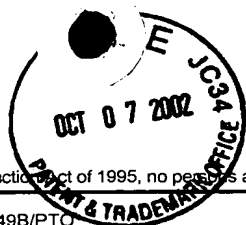
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WV	AA	5,761,115	06/02/1998	Kozicki et al.	
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WV	BA	WO 02/21542	03/14/2002	Kozicki et al.	
	BB	WO 00/48196	08/17/2000	Kozicki et al.	
	BC	WO 97/48032	12/18/1997	Kozicki et al.	
WV	BD	WO 99/28914	06/10/1999	Kozicki et al.	
Examiner Signature	Huan Hoang			Date Considered	1/18/03

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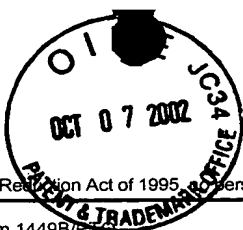
¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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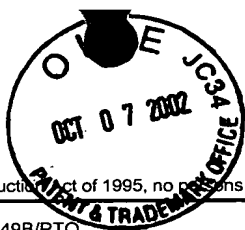
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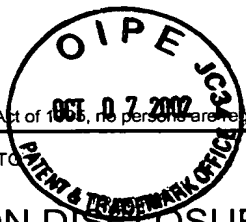
Substitute for form 1449B/P-10 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known		
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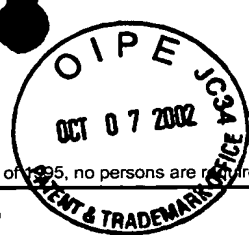
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